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a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer;

a wiring pattern adhered to said surface of said adhesive layer and partially bonded to said bump; and

an insulating and covering layer for insulating and covering said wiring pattern and selectively opening to form an external connecting potion.

7. (Amended) A semiconductor apparatus comprising:

two or more semiconductor devices, each of said devices comprising:

a semiconductor chip;

an adhesive layer provided on a surface of said semiconductor chip on which an electrode is formed; and

a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer,

wherein part of a surface of one of said semiconductor devices on which said adhesive layer is provided is adhered to part or all of a surface of another one of said semiconductor devices on which said adhesive layer is provided and said one and said another on of said semiconductor devices are electrically connected to each other with said bumps at the adhesion surface.

8. (Amended) A semiconductor apparatus comprising:

two or more stacked semiconductor devices, each of said devices comprising:

a semiconductor chip having electrodes formed on the front and back;

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an adhesive layer provided on the front or back of said semiconductor chip;

a bump provided on said electrode of said semiconductor chip and exposed at a surface of said adhesive layer,

wherein one of said semiconductor devices is adhered to an underlaying one of said semiconductor devices through said adhesive layer and the electrodes thereof are connected to each other through said bump.

9. (Amended) The semiconductor device according to claim 1, wherein said adhesive layer comprises a thermoplastic resin with adhesion.

ଧିତ- ଅ Please add new claims-25-30 as follows:

- 25. (Newly Added) A semiconductor device according to claim 1, wherein a top of said stud bump protrudes from a lower surface of said adhesive layer.- -

- 26. (Newly Added) A semiconductor device according to claim 1, wherein said stud bump has a surface which is lower than a surface of said adhesive layer.

- 27: (Newly Added) A semiconductor device according to claim 1, wherein said stud bump comprises gold.- -

- -28: (Newly Added) A semiconductor device according to claim 1, wherein said adhesive layer comprises a thermosetting adhesive layer.- -

Rule

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